

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27161	Application No. 10/605,672	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Bruce B. DORIS <i>et al.</i>		
				Filing Date October 16, 2003		Group 2812
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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EXAMINER	<i>Stavetta dease</i>			DATE CONSIDERED	<i>6/23/06</i>	
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